International IOR Rectifier

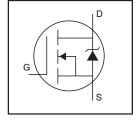
AUTOMOTIVE GRADE

AUIRLR024N AUIRLU024N

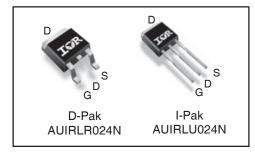
HEXFET® Power MOSFET

Features

- Advanced Planar Technology
- Low On-Resistance
- Logic-Level Gate Drive
- Dynamic dV/dT Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Repetitive Avalanche Allowed up to Timax
- Lead-Free, RoHS Compliant
- Automotive Qualified *



V _{(BR)DSS}	55V
R _{DS(on)} max.	0.065Ω
I _D	17A



G	D	S
Gate	Drain	Source

Description

Specifically designed for Automotive applications, this Cellular design of HEXFET® Power MOSFETs utilizes the latest processing techniques to achieve low onresistance per silicon area. This benefit combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in Automotive and a wide variety of other applications.

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is 25°C, unless otherwise specified.

	Parameter	Max.	Units
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V	17	
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V	12	Α
I _{DM}	Pulsed Drain Current ①	72	
P _D @T _C = 25°C	Power Dissipation	45	W
	Linear Derating Factor	0.3	W/°C
V_{GS}	Gate-to-Source Voltage	± 16	V
E _{AS}	Single Pulse Avalanche Energy ②	68	mJ
I _{AR}	Avalanche Current ①	11	А
E _{AR}	Repetitive Avalanche Energy ①	4.5	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.0	V/ns
TJ	Operating Junction and	-55 to + 175	
T _{STG}	Storage Temperature Range		°C
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

Thermal Resistance

	Parameter	Тур.	Max.	Units
$R_{\theta JC}$	Junction-to-Case		3.3	
$R_{\theta JA}$	Junction-to-Ambient (PCB mount) **		50	°C/W
$R_{\theta JA}$	Junction-to-Ambient		110	

HEXFET® is a registered trademark of International Rectifier.

^{*}Qualification standards can be found at http://www.irf.com/

Static Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Тур.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	55			V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient		0.061		V/°C	Reference to 25°C, I _D = 1mA
				0.065		V _{GS} = 10V, I _D = 10A ④
R _{DS(on)}	Static Drain-to-Source On-Resistance			0.080	Ω	V _{GS} = 5.0V, I _D = 10A ⊕
				0.110		V _{GS} = 4.0V, I _D = 9.0A ④
V _{GS(th)}	Gate Threshold Voltage	1.0		2.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
gfs	Forward Transconductance	8.3			S	$V_{DS} = 25V, I_D = 11A$
I _{DSS}	Drain-to-Source Leakage Current			25	μΑ	$V_{DS} = 55V, V_{GS} = 0V$
				250		$V_{DS} = 44V, V_{GS} = 0V, T_{J} = 150^{\circ}C$
I _{GSS}	Gate-to-Source Forward Leakage			100	nA	V _{GS} = 16V
	Gate-to-Source Reverse Leakage			-100	Ī	V _{GS} = -16V

Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

_ ,		(
Q_g	Total Gate Charge			15		I _D = 11A
Q _{gs}	Gate-to-Source Charge			3.7	nC	$V_{DS} = 44V$
Q_{gd}	Gate-to-Drain ("Miller") Charge			8.5	Ī	V _{GS} = 5.0V,See Fig 6 and 13 ⊕®
t _{d(on)}	Turn-On Delay Time		7.1			V _{DD} = 28V
t _r	Rise Time		74		Ī	I _D = 11A
t _{d(off)}	Turn-Off Delay Time		20		ns	$R_{G} = 12 \Omega, V_{GS} = 5.0V$
t _f	Fall Time		29		Ī	$R_D = 2.4\Omega$, See Fig.10 $@6$
L _D	Internal Drain Inductance		4.5		nH	Between lead, 6mm (0.25in.)
L _S	Internal Source Inductance		7.5			from package and center of die contact
C _{iss}	Input Capacitance		480			V _{GS} = 0V
C _{oss}	Output Capacitance		130		рF	$V_{DS} = 25V$
C _{rss}	Reverse Transfer Capacitance		61		Ī	f = 1.0MHz, See Fig.5 ©

Diode Characteristics

	Parameter	Min.	Тур.	Max.	Units	Conditions	
I _S	Continuous Source Current			17		MOSFET symbol	
	(Body Diode)		17		Α	showing the	
I _{SM}	Pulsed Source Current			72		integral reverse	
	(Body Diode) ①			12		p-n junction diode.	
V_{SD}	Diode Forward Voltage			1.3	V	$T_J = 25^{\circ}C$, $I_S = 11A$, $V_{GS} = 0V$ @	
t _{rr}	Reverse Recovery Time		60	90	ns	$T_J = 25^{\circ}C, I_F = 11A$	
Q _{rr}	Reverse Recovery Charge		130	200	nC	di/dt = 100A/µs ⊕	
t _{on}	Forward Turn-On Time	Intrinsic	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- $@~V_{DD}$ = 25V, starting T_J = 25°C, L = 790µH, R_G = 25 $\Omega,~I_{AS}$ = 11A. (See Figure 12)
- $\ensuremath{ \Im \ } I_{SD} \leq 11A, \ di/dt \leq 290A/\mu s, \ V_{DD} \leq V_{(BR)DSS}, \ T_J \leq 175 ^{\circ} C$
- 4 Pulse width $\leq 300 \mu s$; duty cycle $\leq 2\%$
- $\ensuremath{\mathfrak{D}}$ This is applied for I-PAK, $\ensuremath{L_S}$ of D-PAK is measured between lead and center of die contact .
- © Uses IRLZ24N data and test conditions.

^{**} When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994

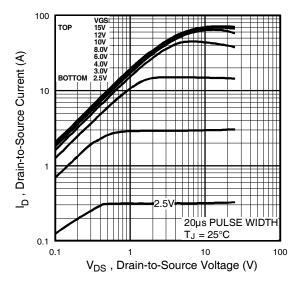
Qualification Information[†]

		Automotive (per AEC-Q101) ††				
		Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.				
Majatura Canajtivitu Laval		D PAK	MSL1			
Woisture Serisii	Moisture Sensitivity Level		I-PAK N/A			
	Machine Model		Class M2(+/-150V) ^{†††}			
		AEC-Q101-002				
ESD	Human Body Model	Class H1A(+/-500V) ^{†††}				
E3D		AEC-Q101-001				
	Charged Device		Class C5(+/-2000V) ^{†††}			
	Model	AEC-Q101-005				
RoHS Complian	nt		Yes			

[†] Qualification standards can be found at International Rectifier's web site: http://www.irf.com/

^{††} Exceptions to AEC-Q101 requirements are noted in the qualification report.

^{†††} Highest passing voltage



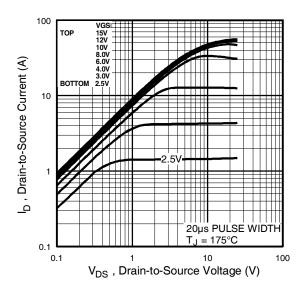
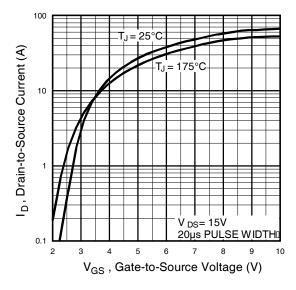


Fig 1. Typical Output Characteristics

Fig 2. Typical Output Characteristics



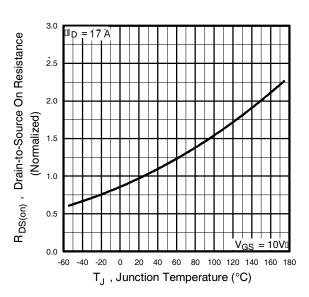
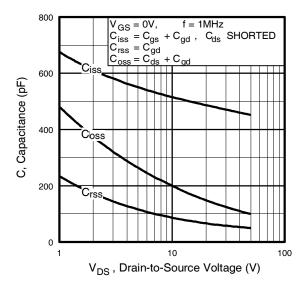


Fig 3. Typical Transfer Characteristics

Fig 4. Normalized On-Resistance Vs. Temperature



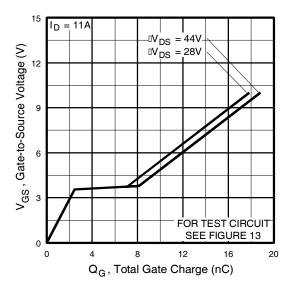
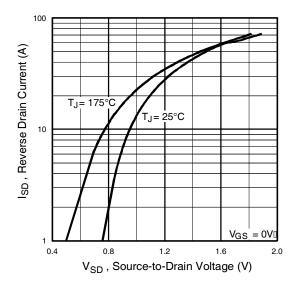


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage





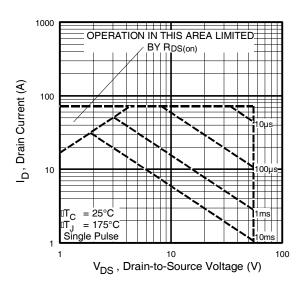


Fig 8. Maximum Safe Operating Area

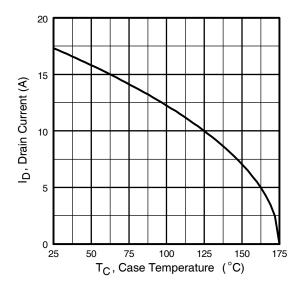


Fig 9. Maximum Drain Current Vs. Case Temperature

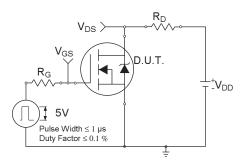


Fig 10a. Switching Time Test Circuit

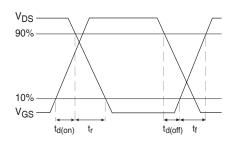


Fig 10b. Switching Time Waveforms

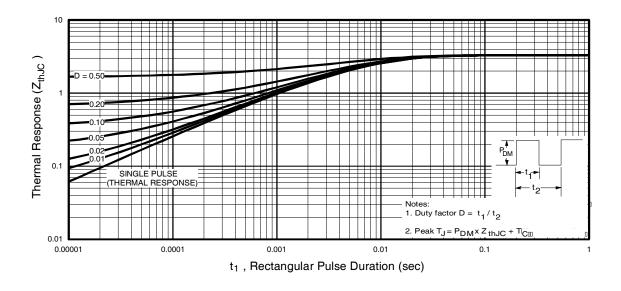


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

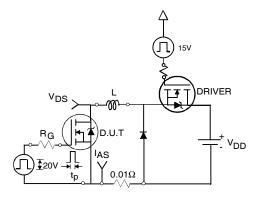


Fig 12a. Unclamped Inductive Test Circuit

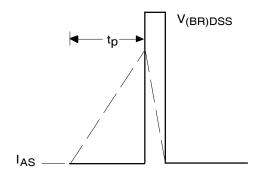


Fig 12b. Unclamped Inductive Waveforms

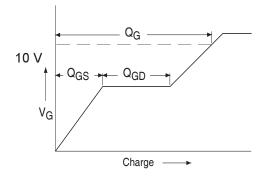


Fig 13a. Basic Gate Charge Waveform

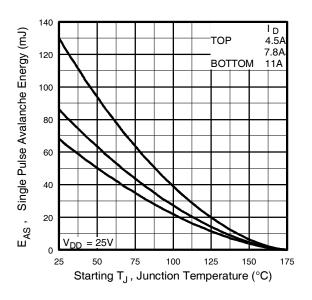


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

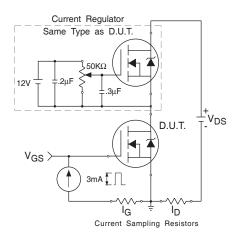
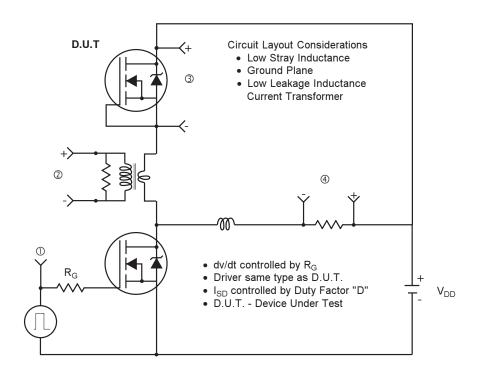
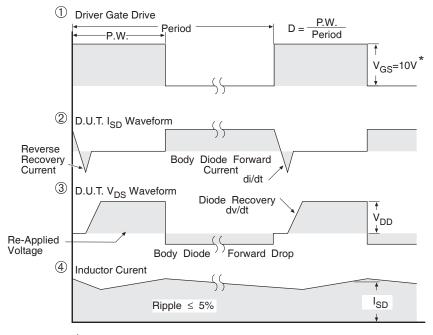


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



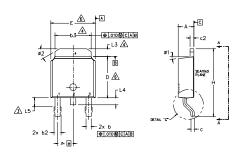


* V_{GS} = 5V for Logic Level Devices

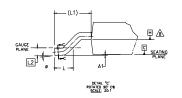
Fig 14. For N-Channel HEXFET® MOSFETs

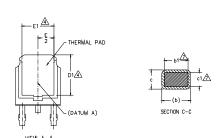
D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)









- 1.- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
- 2.- DIMENSION ARE SHOWN IN INCHES [MILLIMETERS].
- A- LEAD DIMENSION UNCONTROLLED IN L5.
- A- DIMENSION D1, E1, L3 & b3 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
- 5.- SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 AND 0.10 [0.13 AND 0.25] FROM THE LEAD TIP.
- 6- DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005 [0.13] PER SIDE, THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
- ⚠- DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
- 9.- OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

S Y M		DIMENSIONS						
₩ B O	MILLIM	ETERS	INC	HES	O T			
L	MIN.	MAX.	MIN.	MAX.	Ë S			
Α	2.18	2.39	.086	.094				
A1	-	0.13	-	.005				
b	0.64	0.89	.025	.035				
ь1	0.65	0.79	.025	.031	7			
b2	0.76	1,14	.030	.045				
ь3	4.95	5.46	.195	.215	4			
С	0.46	0,61	.018	.024				
c1	0.41	0.56	.016	.022	7			
с2	0.46	0.89	.018	.035				
D	5.97	6.22	.235	.245	6			
D1	5.21	-	.205	-	4			
Ε	6.35	6.73	.250	.265	6			
E1	4.32	_	.170	-	4			
е	2.29	BSC	.090	BSC				
Н	9,40	10.41	.370	.410				
L	1.40	1.78	.055	.070				
L1	2.74	BSC	.108	REF.				
L2	0.51	BSC	.020	BSC				
L3	0.89	1,27	.035	.050	4			
L4	-	1,02	-	.040				
L5	1,14	1.52	.045	.060	3			
ø	0,	10°	0,	10°				
ø1	0*	15⁺	0,	15*				
ø2	25'	35*	25'	35*				

LEAD ASSIGNMENTS

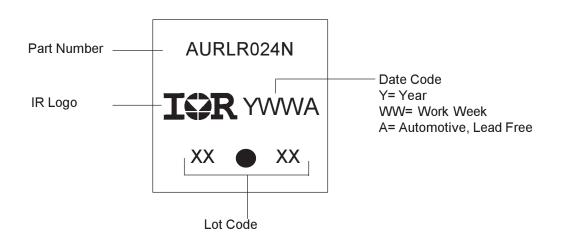
<u>HEXFET</u>

- 1.- GATE 2.- DRAIN 3.- SOURCE
- 4.- DRAIN

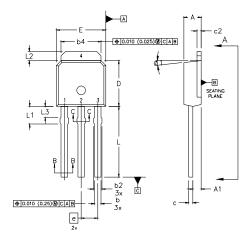
IGBT & CoPAK

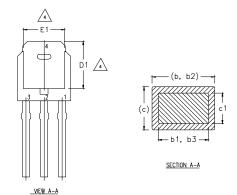
- 2.- COLLECTOR
 3.- EMITTER
 4.- COLLECTOR

D-Pak (TO-252AA) Part Marking Information



I-Pak (TO-251AA) Package Outline (Dimensions are shown in millimeters (inches)





NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
- DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES],
- DIMENSION D & E DO NOT INCLUDE MOLD FLASH, MOLD FLASH SHALL NOT EXCEED 0.005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
 THERMAL PAD CONTOUR OPTION WITHIN DIMENSION 64, L2, E1 & D1.
- LEAD DIMENSION UNCONTROLLED IN L3.
- DIMENSION 61, 63 APPLY TO BASE METAL ONLY. OUTLINE CONFORMS TO JEDEC OUTLINE TO-251AA. CONTROLLING DIMENSION: INCHES.

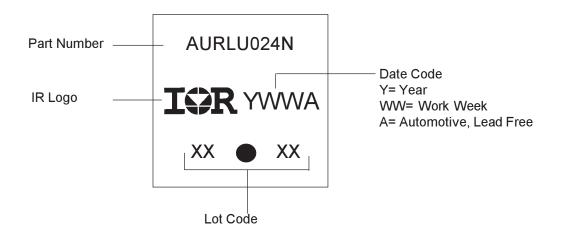
		DIMEN	ISIONS		
SYMBOL	MILLIM	ETERS	INC	HES	
	MIN.	MAX.	MIN.	MAX.	NOTES
A	2,18	2.39	0,086	.094	
A1	0.89	1,14	0.035	0.045	
b	0.64	0.89	0.025	0.035	
ь1	0.64	0.79	0.025	0.031	4
b2	0.76	1,14	0.030	0.045	
b3	0.76	1,04	0.030	0.041	
b4	5.00	5.46	0.195	0.215	4
С	0.46	0.61	0.018	0.024	
c1	0.41	0.56	0.016	0.022	
c2	.046	0.86	0.018	0.035	
D	5.97	6.22	0.235	0.245	3, 4
D1	5,21	-	0,205	-	4
E	6.35	6.73	0.250	0.265	3, 4
E1	4,32	-	0,170	-	4
e	2.	29	0,090	BSC	
L	8.89	9.60	0.350	0.380	
L1	1,91	2.29	0,075	0.090	
L2	0.89	1,27	0,035	0.050	4
L3	1,14	1.52	0.045	0.060	5
ø1	0*	151	0,	15°	

LEAD ASSIGNMENTS

HEXFET

- 1 GATE
- 2.- DRAIN 3.- SOURCE 4.- DRAIN

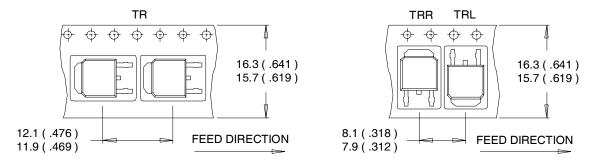
I-Pak (TO-251AA) Part Marking Information



Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

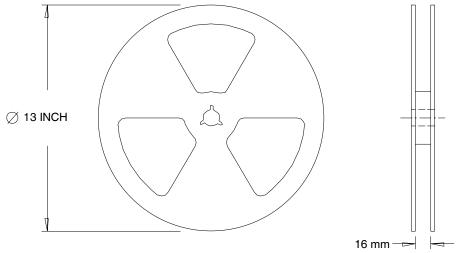
D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



NOTES:

- 1. CONTROLLING DIMENSION: MILLIMETER.
- 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
- 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES:

1. OUTLINE CONFORMS TO EIA-481.

Ordering Information

Base part	Package Type	Standard Pack		Complete Part Number
		Form	Quantity	
AUIRLR024N	DPak	Tube	75	AUIRLR024N
		Tape and Reel	2000	AUIRLR024NTR
		Tape and Reel Left 300		AUIRLR024NTRL
		Tape and Reel Right	3000	AUIRLR024NTRR
AUIRLU024N	IPak	Tube	75	AUIRLU024N

International

TOR Rectifier

AUIRLR/U024N

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IR products are neither designed nor intended for use in automotive applications or environments unless the specific IR products are designated by IR as compliant with ISO/TS 16949 requirements and bear a part number including the designation "AU". Buyers acknowledge and agree that, if they use any non-designated products in automotive applications, IR will not be responsible for any failure to meet such requirements

For technical support, please contact IR's Technical Assistance Center http://www.irf.com/technical-info/

WORLD HEADQUARTERS:

233 Kansas St., El Segundo, California 90245 Tel: (310) 252-7105